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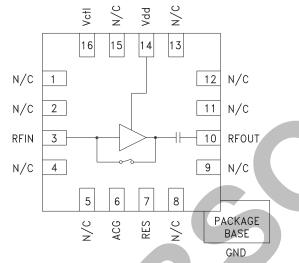
GaAs PHEMT MMIC LNA w/ FAILSAFE BYPASS MODE, 700 - 1200 MHz

#### **Typical Applications**

The HMC668LP3(E) is ideal for:

- Cellular/3G and LTE/WiMAX/4G
- BTS & Infrastructure
- Repeaters and Femtocells
- Tower Mounted Amplifiers
- Test & Measurement Equipment

#### **Functional Diagram**



#### Features

Noise Figure: 0.9 dB Output IP3: +33 dBm Gain: 16 dB Failsafe Operation: Bypass is enabled when LNA is unpowered Single Supply: +3V or +5V

16 Lead 3x3mm QFN Package: 9 mm<sup>2</sup>

#### **General Description**

The HMC668LP3(E) is a versatile, high dynamic range GaAs MMIC Low Noise Amplifier that integrates a low loss LNA bypass mode on the IC. The amplifier is ideal for receivers and LNA modules operating between 0.7 and 1.2 GHz and provides 0.9 dB noise figure, 16 dB of gain and +33 dBm IP3 from a single supply of +5V @ 57mA. Input and output return losses are excellent and no external matching components are required. A single control line is used to switch between LNA mode and a low loss bypass mode. The failsafe topology enables the LNA bypass path, when no DC power is available. The HMC668LP3(E) offers improved noise figure versus the previously released HMC373LP3(E).

#### Electrical Specifications, $T_{A} = +25^{\circ}$ C, Rbias = 0 Ohm LNA Mode **Bypass Mode** Failsafe Mode Parameter Vdd = +3VVdd = +5VUnits Min. Тур. Max Min. Тур. Max. Min. Тур. Max. Min. Тур. Max. Frequency Range 0.7 - 1.2 0.7 - 1.2 0.7 - 1.2 0.7 - 1.2 GHz Gain 12 15 13 16 -2.5 -1.5 -2.5 -1.5 dB Gain Variation Over Temperature 0.03 0.016 0.0008 0.0008 dB / °C Noise Figure 0.85 1.1 0.9 1.1 dB 12 12 Input Return Loss 12 13 dB Output Return Loss 13 14 13 13 dB **Reverse Isolation** 22 23 -dB Power for 1dB Compression 13 13 22 24 dBm (P1dB)<sup>[1]</sup> Third Order Intercept (IP3)<sup>[2]</sup> 27 33 26 26 dBm Supply Current (Idd) 32 40 57 70 0.05 mΑ -Switching Speed (90% -10%) 200 LNA Mode to Bypass Mode ns Bypass Mode to LNA Mode 85 85 ns

[1] P1dB for LNA Mode is referenced to RFOUT while P1dB for Bypass and Failsafe Modes are referenced to RFIN. [2] IP3 for LNA Mode is referenced to RFOUT while IP3 for Bypass and Failsafe Modes are referenced to RFIN.

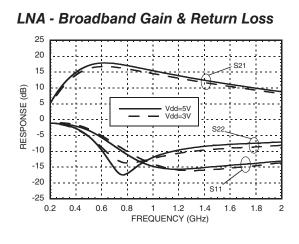
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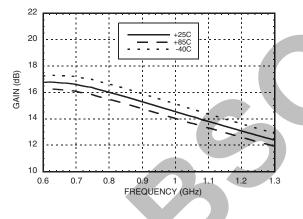
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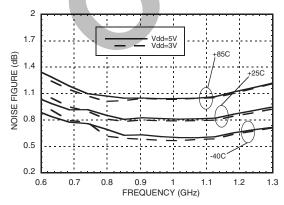
#### GaAs PHEMT MMIC LNA w/ FAILSAFE BYPASS MODE, 700 - 1200 MHz

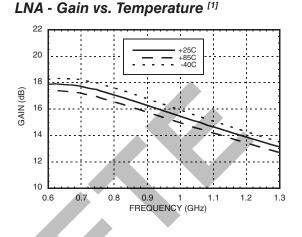


LNA - Gain vs. Temperature [2]

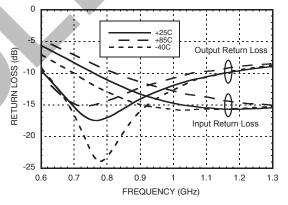


LNA - Noise Figure vs. Temperature [3]

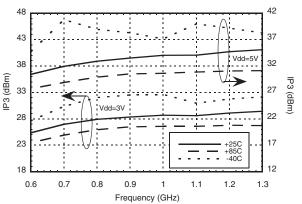




LNA - Return Loss vs. Temperature [1]



LNA - Output IP3 vs. Temperature, Output Power @ 0 dBm



[1] Vdd = 5V [2] Vdd = 3V [3] Measurement reference plane shown on evaluation PCB drawing.

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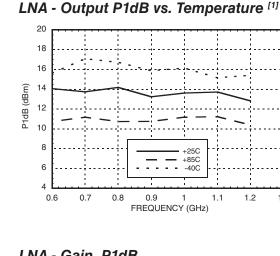
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1.2

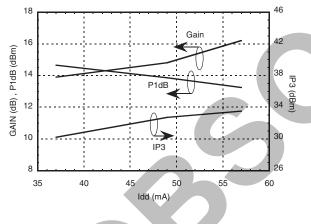
1.3



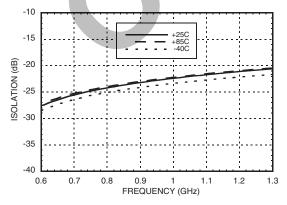
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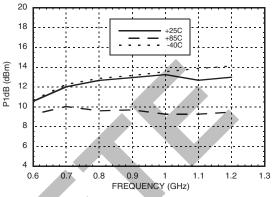
LNA - Gain, P1dB, Output IP3 vs. Current <sup>[1]</sup> @ 900 MHz



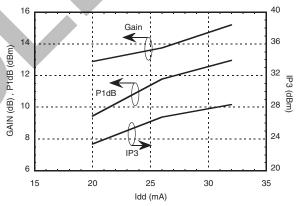
LNA - Reverse Isolation vs. Temperature [1]



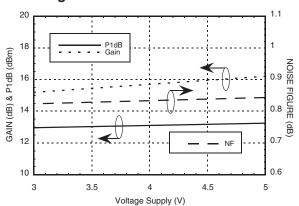








LNA - Output P1dB, Gain & Noise Figure <sup>[3]</sup> vs. Vdd @ 900 MHz



[3] Measurement reference plane shown on evaluation PCB drawing. [1] Vdd = 5V [2] Vdd = 3V

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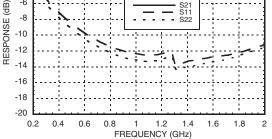


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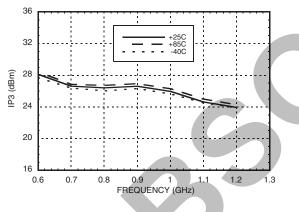
Bypass Mode -

Bypass Mode -Broadband Gain & Return Loss

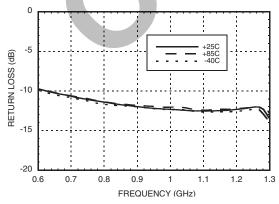
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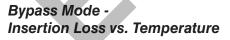
Bypass Mode - Input IP3 vs. Temperature, Output Power @ 5 dBm

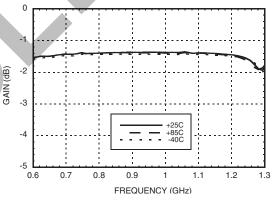


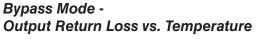
Bypass Mode -Input Return Loss vs. Temperature

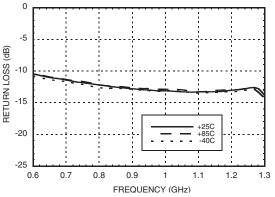


Input IP3 vs. Output Power @ 900 MHz









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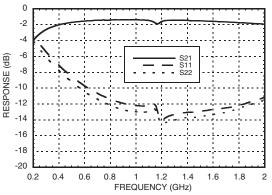
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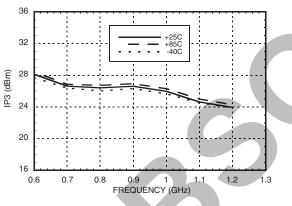
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Failsafe Mode -

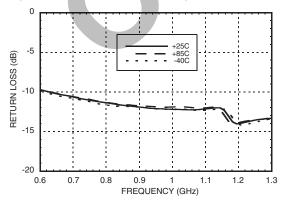
Failsafe Mode -Broadband Gain & Return Loss

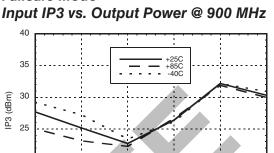


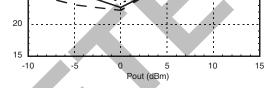
Failsafe Mode - Input IP3 vs. Temperature, Output Power @ 5 dBm



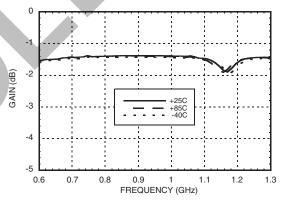
Failsafe Mode -Input Return Loss vs. Temperature



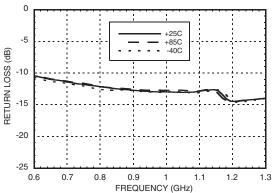




Failsafe Mode -Insertion Loss vs. Temperature



Failsafe Mode -Output Return Loss vs. Temperature



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GaAs PHEMT MMIC LNA w/ FAILSAFE BYPASS MODE, 700 - 1200 MHz

#### Absolute Maximum Ratings

-	
Drain Bias Voltage (Vdd)	+6 Vdc
Control Voltage (Vctl)	+6 Vdc
RF Input PowerLNA Mode(RFIN)Bypass / Failsafe Mode	+5 dBm +20 dBm
Channel Temperature	150 °C
Continuous Pdiss (T = 85 °C) (derate 10.71 mW/°C above 85 °C)	0.70 W
Thermal Resistance (channel to ground paddle)	93.33 °C/W
Storage Temperature	-65 to +150° C
Operating Temperature -40 to +85° C	
ESD Sensitivity (HBM)	Class 1A

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#### Typical Supply Current vs. Vdd

Rbias Ω	ldd (mA)		
	Vdd= 3V	Vdd= 5V	
0	32	57	
15	26	49	
47	20	37	
180 [1]	10	20	

[1] Recommended maximum Rbias



ELECTROSTATIC SENSITIVE DEVICE OBSERVE HANDLING PRECAUTIONS

#### Truth Table

LNA Mode	VctI = Vdd = 3 to 5V
Bypass Mode	Vctl= 0V, Vdd = 3 to 5V
Failsafe Mode	VctI = Vdd = N/C

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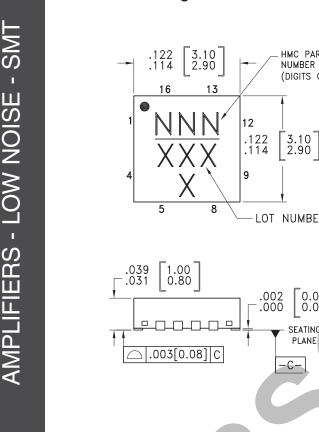


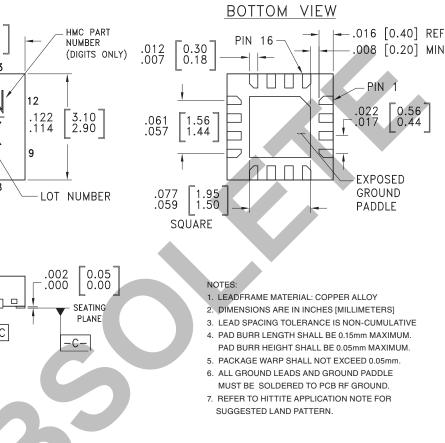
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GaAs PHEMT MMIC LNA w/ FAILSAFE BYPASS MODE, 700 - 1200 MHz

#### **Outline Drawing**





#### **Package Information**

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking [3]
HMC668LP3	Low Stress Injection Molded Plastic	Sn/Pb Solder	MSL1 <sup>[1]</sup>	668 XXXX
HMC668LP3E	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1 <sup>[2]</sup>	<u>668</u> XXXX

[1] Max peak reflow temperature of 235 °C

[2] Max peak reflow temperature of 260 °C

[3] 4-Digit lot number XXXX

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### GaAs PHEMT MMIC LNA w/ FAILSAFE BYPASS MODE, 700 - 1200 MHz

#### **Pin Descriptions**

Pin Number	Function	Description	Interface Schematic
1, 2, 4, 5, 8, 9, 11, 12, 13, 15	N/C	No connection required. These pins may be connected to RF GND. Performance will not be affected.	
3	RFIN	This pin is DC coupled. Off-chip DC blocking capacitor required.	
6	ACG	AC Ground. Attach bypass capacitor per application circuit.	
7	RES	External resistor pin for current control. See table for external resistor value vs. bias current data.	ESD ACG RES
10	RFOUT	This pin is matched to 50 Ohms	
14	Vdd	Power Supply voltage pin. External bypass capacitors required.	Vdd Q
16	Vctl	Control voltage pin for LNA / Bypass Modes. Setting voltage equal to VDD enables LNA Mode. External Bypass capacitor required.	VctI ESD ESD ESD

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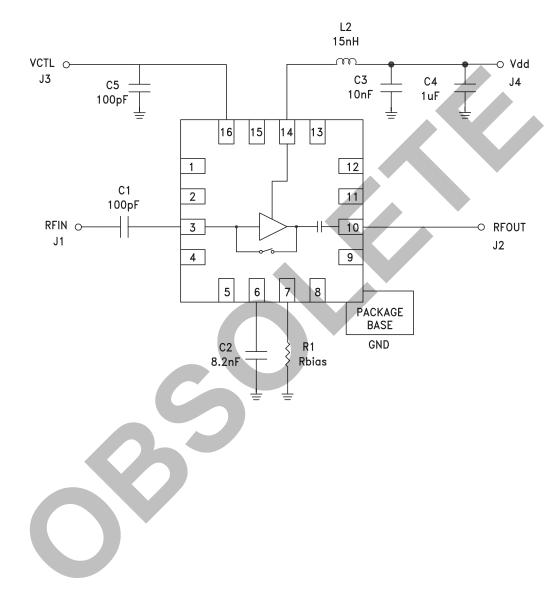


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#### Application Circuit



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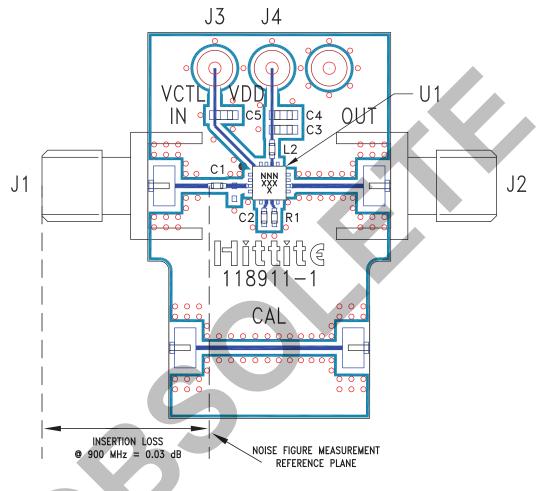


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#### GaAs PHEMT MMIC LNA w/ FAILSAFE BYPASS MODE, 700 - 1200 MHz

#### **Evaluation PCB**



#### List of Materials for Evaluation PCB 121922 [1]

Item	Description	
J1 - J2	PCB Mount SMA Connector	
J3 - J4	DC Pin	
C1	100 pF Capacitor, 0402 Pkg.	
C2	8200 pF Capacitor, 0402 Pkg.	
C3	10 nF Capacitor, 0603 Pkg.	
C4	1 μF Capacitor, 0603 Pkg.	
C5	100 pF Capacitor, 0603 Pkg.	
L2	15 nH Inductor, 0402 Pkg.	
R1	0 Ohm Resistor, 0402 Pkg.	
U1	HMC668LP3(E) Amplifier	
PCB [2]	118911 Evaluation Board	

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350

The circuit board used in the application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation circuit board shown is available from Hittite upon request.

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